

GSDSK22A Series

Surface Mount Schottky Barrier Rectifiers

Product Description

Reverse Voltage 20V to 200V
Forward Current 2.0A

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O
- For surface mounted applications
- High current capacity
- Built-in strain relief
- Low profile package
- Metal to silicon rectifier. majority carrier conduction
- High surge capacity
- Low power loss, high efficiency
- For use in low voltage high frequency inverters, free wheeling, and polarity protection application
- Halogen-free parts.

Mechanical Data

- Case : Molded plastic, DO-214AC(SMA)
- Terminals : Solder plated, solderable per MIL-STD-750, method 2026 guaranteed
- Polarity : Color band denotes cathode end

Packages



SMA

Ordering Information



Part Number	Package	Quantity Reel
GSDSK2XAF	SMA	5000 PCS

Marking Information

P/N	Part Marking	Package
GSDSK22AF	SK22	SMA (DO-214AC)
GSDSK23AF	SK23	SMA (DO-214AC)
GSDSK24AF	SK24	SMA (DO-214AC)
GSDSK25AF	SK25	SMA (DO-214AC)
GSDSK26AF	SK26	SMA (DO-214AC)
GSDSK28AF	SK28	SMA (DO-214AC)
GSDSK210AF	SK210	SMA (DO-214AC)
GSDSK215AF	SK215	SMA (DO-214AC)
GSDSK220AF	SK220	SMA (DO-214AC)

Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60HZ, resistive or inductive load.

For capacitive load, derate current by 20%.

Symbol	Conditions	GSDSK22AF	GSDSK23AF	GSDSK24AF	Unit
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	20	30	40	V
V_{RMS}	Maximum RMS Voltage	14	21	28	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	V
V_F	Maximum Instantaneous $I_F=2.0A$ (Note 1)	0.50	0.55		V
I_F	Maximum Average Forward Rectified Current	2.0			A
I_{FSM}	Peak Forward Surge Current, 8.3ms Single Half Sine-Wave Superimposed on Rated Load	50			A
I_R	Maximum DC Reverse Current At Rated DC Blocking Voltage	$T_A=25^{\circ}C$	0.5		mA
		$T_A=100^{\circ}C$	20		
$R_{\theta JA}$	Typical Thermal Resistance (Note 2)	75			$^{\circ}C/W$
$R_{\theta JL}$		17			$^{\circ}C/W$
T_J	Operating Junction Temperature Range	-65 to +125			$^{\circ}C$
T_{STG}	Storage Temperature Range	-65 to +150			$^{\circ}C$

Notes 1 : Pulse test: 300 μ s pulse width, 1% duty cycle.

Notes 2 : P.C.B. mounted with 0.3 x 0.3" (8.0 x 8.0mm) copper pad areas.

Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60HZ, resistive or inductive load.

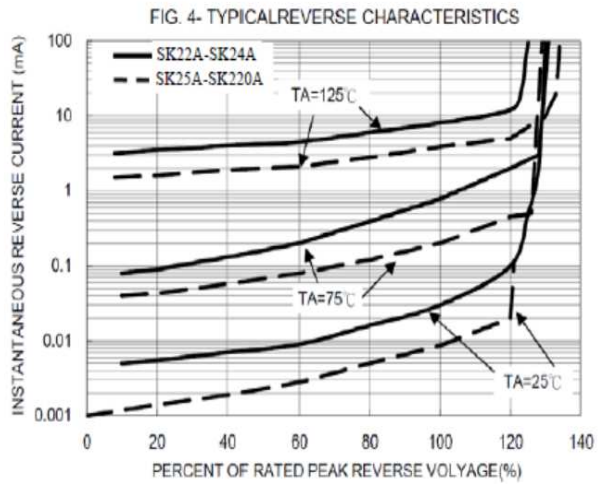
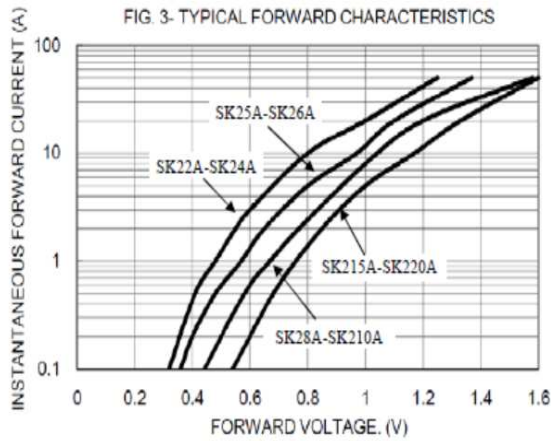
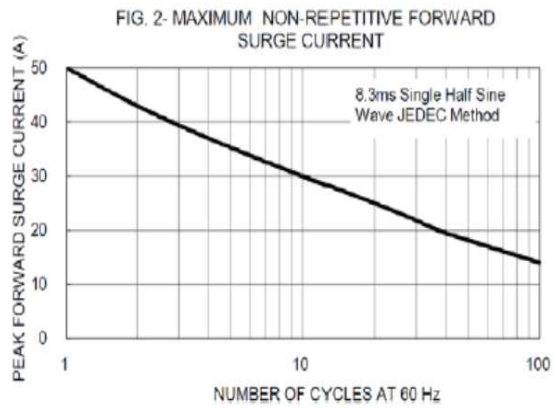
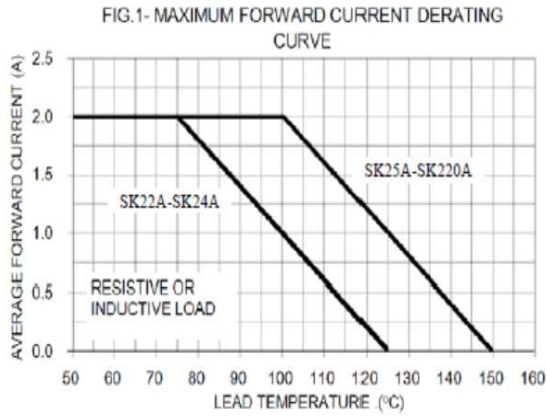
For capacitive load, derate current by 20%.

Symbol	Conditions	GSDSK25AF	GSDSK26AF	GSDSK28AF	Unit
V _{RRM}	Maximum Repetitive Peak Reverse Voltage	50	60	80	V
V _{RMS}	Maximum RMS Voltage	35	42	56	V
V _{DC}	Maximum DC Blocking Voltage	50	60	80	V
V _F	Maximum Instantaneous I _F =2.0A (Note 1)	0.75		0.85	V
Symbol	Conditions	GSDSK210AF	GSDSK215AF	GSDSK220AF	Unit
V _{RRM}	Maximum Repetitive Peak Reverse Voltage	100	150	200	V
V _{RMS}	Maximum RMS Voltage	71	105	140	V
V _{DC}	Maximum DC Blocking Voltage	100	150	200	V
V _F	Maximum Instantaneous I _F =2.0A (Note 1)	0.85	0.95		V
I _F	Maximum Average Forward Rectified Current	2.0			A
I _{FSM}	Peak Forward Surge Current, 8.3ms Single Half Sine-Wave Superimposed on Rated Load	50			A
I _R	Maximum DC Reverse Current At Rated DC Blocking Voltage	T _A = 25°C	0.5		mA
		T _A = 100°C	20		
R _{θJA}	Typical Thermal Resistance (Note 2)	75			°C/W
R _{θJL}		17			°C/W
T _J	Operating Junction Temperature Range	-65 to +125			°C
T _{STG}	Storage Temperature Range	-65 to +150			°C

Notes 1 : Pulse test: 300µs pulse width, 1% duty cycle.

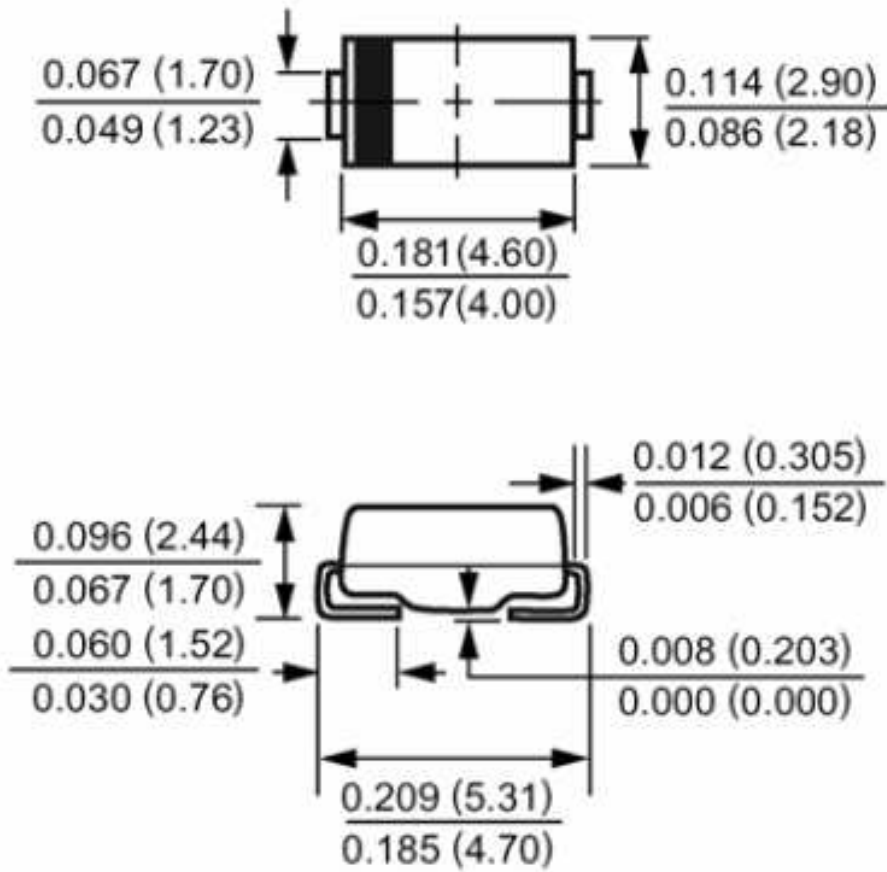
Notes 2 : P.C.B. mounted with 0.3 x 0.3" (8.0 x 8.0mm) copper pad areas.

Typical Characteristics



Package Dimension

DO-214AC(SMA)









Dimensions in inches and (millimeters)

NOTICE

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587